

30 V, 350 mA dual N-channel Trench MOSFET Rev. 1 — 1 August 2011

Product data sheet

Product profile 1.

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- ESD protection up to 2 kV
- AEC-Q101 qualified
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|--------------|-----|-----|------|
| Per transi | stor | | | | | |
| V _{DS} | drain-source voltage | T _j = 25 °C | - | - | 30 | V |
| V _{GS} | gate-source voltage | | -8 | - | 8 | V |
| I _D | drain current | V_{GS} = 4.5 V; T_{amb} = 25 °C | <u>[1]</u> _ | - | 350 | mA |
| Static cha | racteristics (per transist | or) | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 4.5 V; I _D = 350 mA; T _j = 25 °C | - | 1 | 1.4 | Ω |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

| Table 2. | Pinning | g information | | |
|----------|---------|---------------|--------------------|---|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | S1 | source TR1 | | 54 52 |
| 2 | G1 | gate TR1 | | |
| 3 | D2 | drain TR2 | | |
| 4 | S2 | source TR2 | | $G1 \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$ |
| 5 | G2 | gate TR2 | | |
| 6 | D1 | drain TR1 | SOT363 (SC-88) | |
| | | | | S1 S2 017aaa256 |

3. Ordering information

| Table 3. Ordering | g information | | |
|-------------------|---------------|--|---------|
| Type number | Package | | |
| | Name | Description | Version |
| NX3008NBKS | SC-88 | plastic surface-mounted package; 6 leads | SOT363 |

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| NX3008NBKS | LB% |

[1] % = placeholder for manufacturing site code.

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------------|--|--------------|------|------|
| Per transis | stor | | | | |
| V _{DS} | drain-source voltage | T _j = 25 °C | - | 30 | V |
| V _{GS} | gate-source voltage | | -8 | 8 | V |
| I _D | drain current | V_{GS} = 4.5 V; T_{amb} = 25 °C | <u>[1]</u> _ | 350 | mA |
| | | $V_{GS} = 4.5 \text{ V}; \text{ T}_{amb} = 100 \text{ °C}$ | <u>[1]</u> _ | 230 | mA |
| I _{DM} | peak drain current | $T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$ | - | 1.4 | А |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | 280 | mW |
| | | | <u>[1]</u> _ | 320 | mW |
| | | T _{sp} = 25 °C | - | 990 | mW |
| Per device | • | | | | |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | 445 | mW |
| Tj | junction temperature | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | -55 | 150 | °C |
| T _{stg} | storage temperature | | -65 | 150 | °C |
| Source-dra | ain diode | | | | |
| I _S | source current | T _{amb} = 25 °C | - | 300 | mA |
| ESD maxir | num rating | | | | |
| V _{ESD} | electrostatic discharge voltage | НВМ | [3] | 2000 | V |

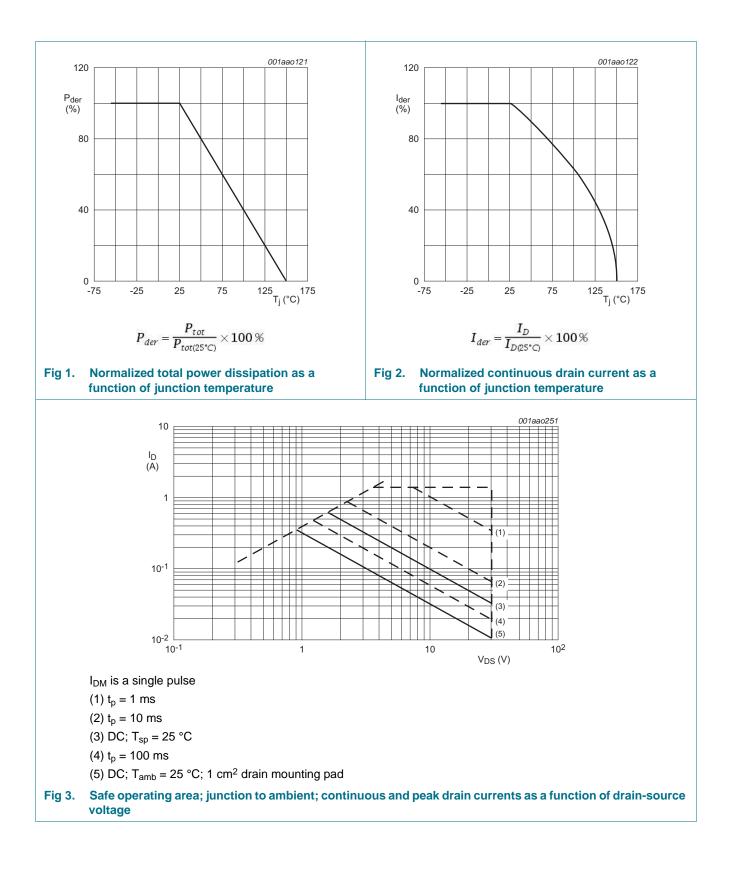
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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NX3008NBKS Product data sheet Table C

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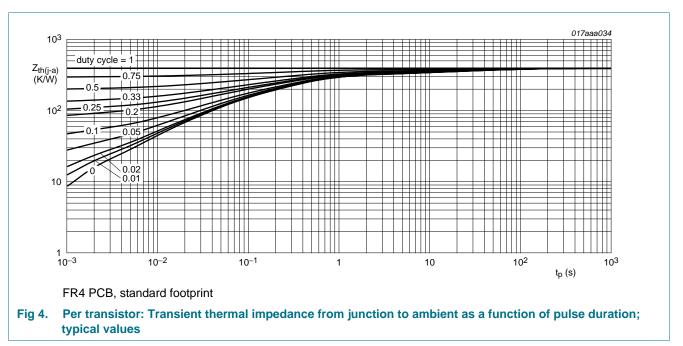
6. Thermal characteristics

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| Table 6. In | nermal characteristics | | | | | |
|-----------------------|--|-------------|--------------|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Per transisto | r | | | | | |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | <u>[1]</u> - | 390 | 445 | K/W |
| | | | [2] _ | 340 | 390 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | - | - | 130 | K/W |
| Per device | | | | | | |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | <u>[1]</u> - | - | 300 | K/W |
| - | | | | | | |

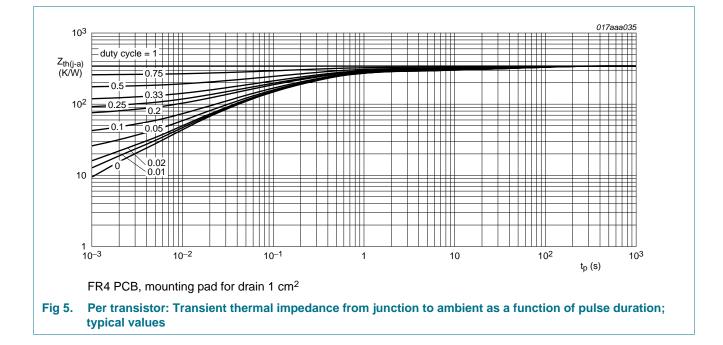
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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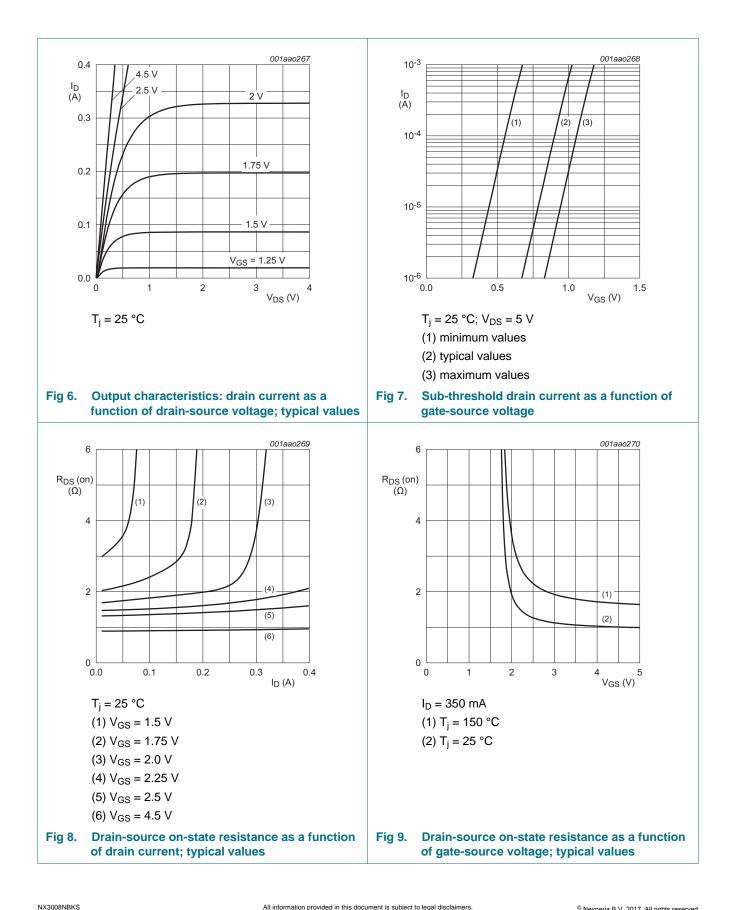
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7. Characteristics

| Table 7. | Characteristics | | | | | |
|----------------------|-----------------------------------|---|------|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
| Static cha | aracteristics (per transistor) | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ | 30 | - | - | V |
| V _{GSth} | gate-source threshold voltage | $I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ | 0.6 | 0.9 | 1.1 | V |
| I _{DSS} | drain leakage current | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| | | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C | - | - | 10 | μA |
| I _{GSS} | gate leakage current | $V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; \text{T}_{j} = 25 ^{\circ}\text{C}$ | - | 0.2 | 1 | μΑ |
| | | $V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.2 | 1 | μΑ |
| | | $V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 10 | - | nA |
| | | V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C | - | 10 | - | nA |
| | | $V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 1 | - | nA |
| | | V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C | - | 1 | - | nA |
| R _{DSon} | drain-source on-state | V _{GS} = 4.5 V; I _D = 350 mA; T _j = 25 °C | - | 1 | 1.4 | Ω |
| | resistance | V _{GS} = 4.5 V; I _D = 350 mA; T _j = 150 °C | - | 1.8 | 2.5 | Ω |
| | | V_{GS} = 2.5 V; I _D = 200 mA; T _j = 25 °C | - | 1.4 | 2.1 | Ω |
| | | V _{GS} = 1.8 V; I _D = 10 mA; T _j = 25 °C | - | 2 | 2.8 | Ω |
| 9 _{fs} | forward transconductance | V_{DS} = 10 V; I _D = 350 mA; T _j = 25 °C | - | 310 | - | mS |
| Dynamic | characteristics (per transist | or) | | | | |
| Q _{G(tot)} | total gate charge | V_{DS} = 15 V; I _D = 350 mA; V _{GS} = 4.5 V; | - | 0.52 | 0.68 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.17 | - | nC |
| Q _{GD} | gate-drain charge | | - | 0.08 | - | nC |
| C _{iss} | input capacitance | V_{DS} = 15 V; f = 1 MHz; V_{GS} = 0 V; | - | 34 | 50 | pF |
| C _{oss} | output capacitance | $T_j = 25 \ ^{\circ}C$ | - | 6.5 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 2.2 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 20 \text{ V}; \text{ R}_{L} = 250 \Omega; V_{GS} = 4.5 \text{ V}; \label{eq:VDS}$ | - | 15 | 30 | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 \ ^{\circ}C$ | - | 11 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 69 | 138 | ns |
| t _f | fall time | | - | 19 | - | ns |
| Source-d | rain diode (per transistor) | | | | | |
| V _{SD} | source-drain voltage | I _S = 350 mA; V _{GS} = 0 V; T _i = 25 °C | 0.47 | 0.85 | 1.2 | V |

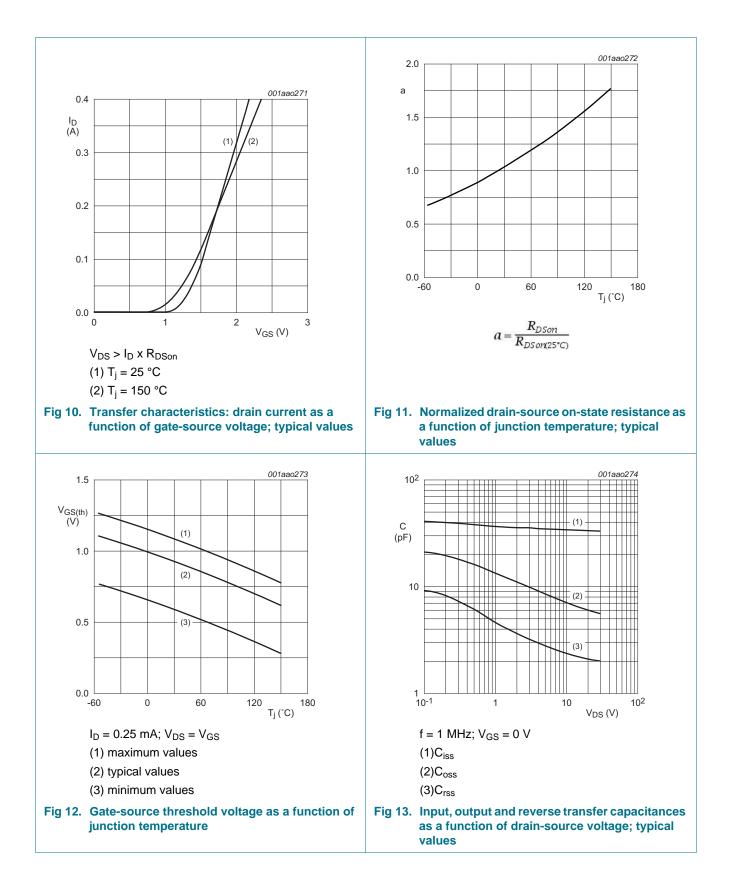
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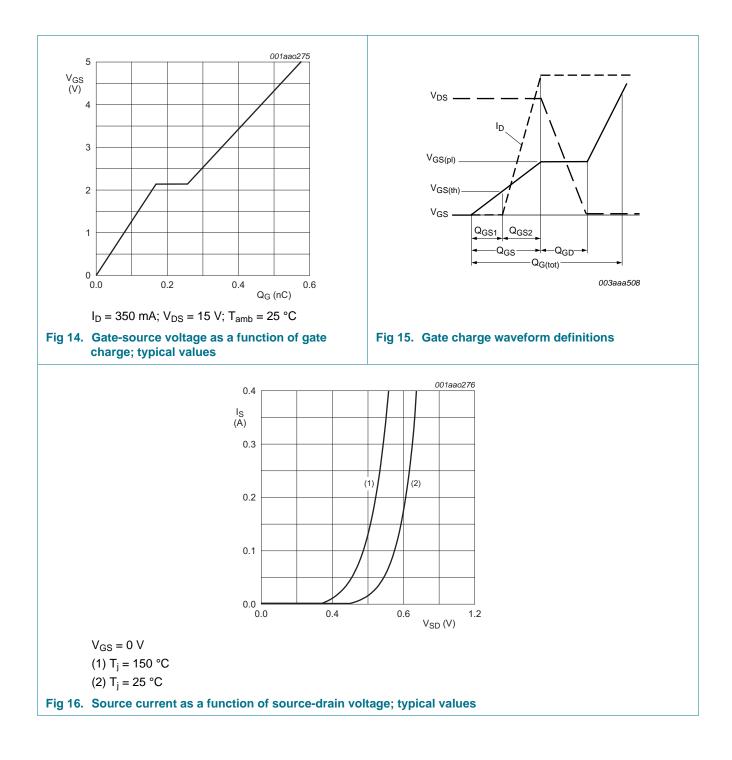
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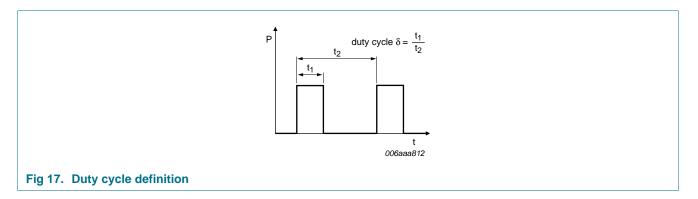
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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline

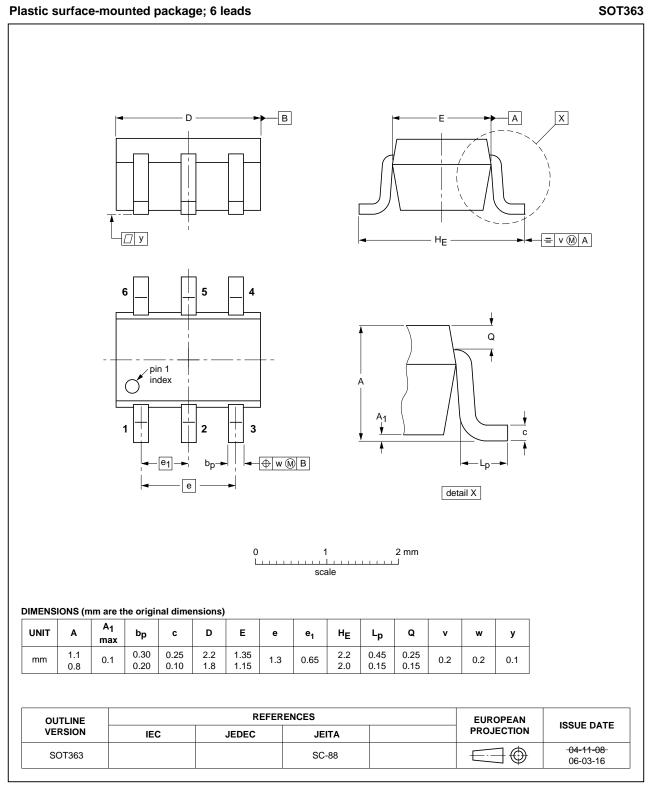


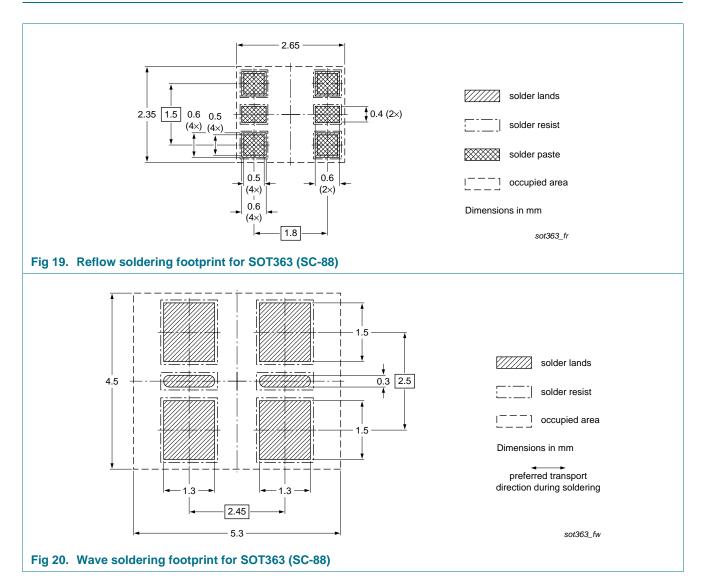
Fig 18. Package outline SOT363 (SC-88)

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10. Soldering



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11. Revision history

| Table 8. Re | Revision history | | | | | |
|-------------|------------------|--------------|--------------------|---------------|------------|--|
| Document ID | | Release date | Data sheet status | Change notice | Supersedes | |
| NX3008NBKS | v.1 | 20110801 | Product data sheet | - | - | |

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12. Legal information

12.1 Data sheet status

| Document status [1] [2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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